

**Silicon Epitaxial Planar Zener Diodes**

**ZMPTZ3V6B...ZMPTZ36B**

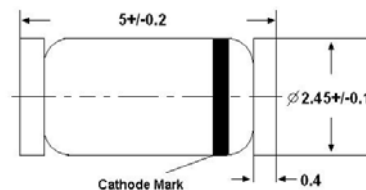
**Features**

- Small surface mounting type
- 1 W of power can be obtained despite compact size
- High surge withstand level

**Applications**

- Voltage regulation and voltage limiting
- Voltage surge absorption

LL-41



Glass case MELF  
Dimensions in mm

**Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)**

Parameter	Symbol	Value	Unit
Power Dissipation	P <sub>tot</sub>	1	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 150	°C

**Characteristics at T<sub>a</sub> = 25 °C (V<sub>F</sub> = 1.2 V Max. at I<sub>F</sub> = 200 mA)**

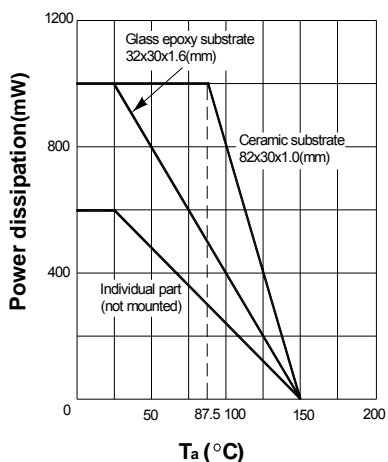
Type	Zener Voltage			Dynamic Resistance		Reverse current	
	V <sub>Z</sub>		at I <sub>ZT</sub>	Z <sub>ZT</sub> (Ω)	at I <sub>ZT</sub>	I <sub>R</sub> (μA)	at V <sub>R</sub>
	Min. (V)	Max. (V)	(mA)	Max.	(mA)	Max.	(V)
ZMPTZ3V6B	3.6	4	40	15	40	20	1
ZMPTZ3V9B	3.9	4.4	40	15	40	20	1
ZMPTZ4V3B	4.3	4.8	40	15	40	20	1
ZMPTZ4V7B	4.7	5.2	40	10	40	20	1
ZMPTZ5V1B	5.1	5.7	40	8	40	20	1
ZMPTZ5V6B	5.6	6.3	40	8	40	20	1.5
ZMPTZ6V2B	6.2	7	40	6	40	20	3
ZMPTZ6V8B	6.8	7.7	40	6	40	20	3.5
ZMPTZ7V5B	7.5	8.4	40	4	40	20	4
ZMPTZ8V2B	8.2	9.3	40	4	40	20	5
ZMPTZ9V1B	9.1	10.2	40	6	40	20	6
ZMPTZ10B	10	11.2	40	6	40	10	7
ZMPTZ11B	11	12.3	20	8	20	10	8
ZMPTZ12B	12	13.5	20	8	20	10	9
ZMPTZ13B	13.3	15	20	10	20	10	10
ZMPTZ15B	14.7	16.5	20	10	20	10	11
ZMPTZ16B	16.2	18.3	20	12	20	10	12
ZMPTZ18B	18	20.3	20	12	20	10	13
ZMPTZ20B	20	22.4	20	14	20	10	15
ZMPTZ22B	22	24.5	10	14	10	10	17
ZMPTZ24B	24	27.6	10	16	10	10	19
ZMPTZ27B	27	30.8	10	16	10	10	21
ZMPTZ30B	30	34	10	18	10	10	23
ZMPTZ33B	33	37	10	18	10	10	25
ZMPTZ36B	36	40	10	20	10	10	27

<sup>1)</sup> Tested with pulses tp = 20 ms.

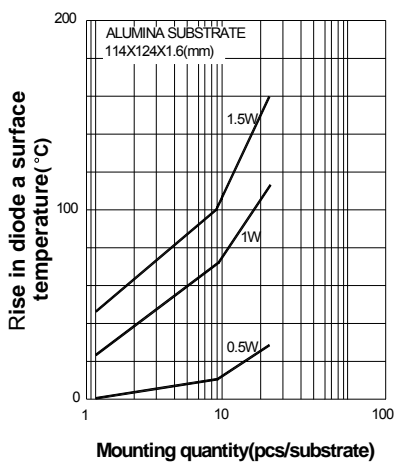
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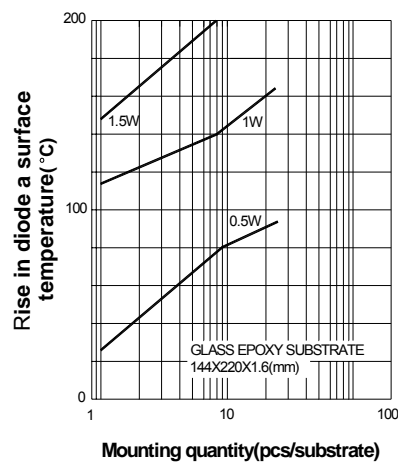
Derating curve



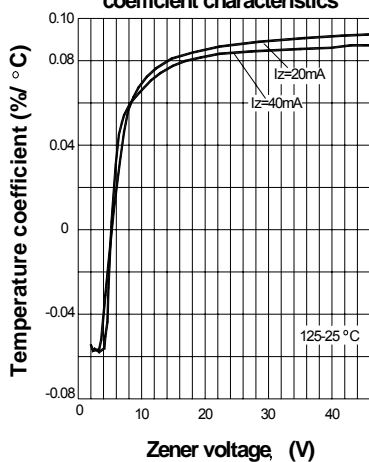
Rise in surface temperature



Rise in surface temperature



Zener voltage - temp. coefficient characteristics



Zener voltage characteristics

